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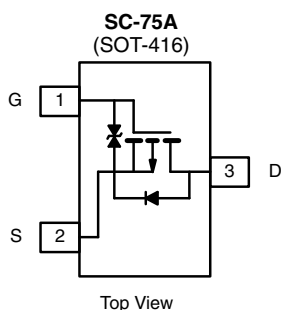
For any questions, you can email us directly:

sales@integrated-circuit.com



P-Channel 60 V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|---------------------------|---------------------------------|-------------------------|---------------------|
| V _{DS(min.)} (V) | R _{DS(on)} (Ω) | V _{GS(th)} (V) | I _D (mA) |
| - 60 | 4.0 at V _{GS} = - 10 V | - 1 to 3.0 | - 190 |



Marking Code: F

Ordering Information: Si1021R-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

BENEFITS

- Ease in Driving Switches
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven without Buffer
- Small Board Area

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | |
|---|-----------------------------------|-------------|------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V _{DS} | - 60 | V |
| Gate-Source Voltage | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 25 °C | - 190 | mA |
| | T _A = 85 °C | - 135 | |
| Pulsed Drain Current ^b | I _{DM} | - 650 | |
| Power Dissipation ^a | T _A = 25 °C | 250 | mW |
| | T _A = 85 °C | 130 | |
| Maximum Junction-to-Ambient ^a | R _{thJA} | 500 | °C/W |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | °C |

Notes:

- Surface mounted on FR4 board.
- Pulse width limited by maximum junction temperature.

Si1021R

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| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|--------------|---|-------|------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$ | - 60 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -0.25\text{ mA}$ | - 1 | | - 3.0 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 10 | μA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$ | | | ± 200 | |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}, T_J = 85\text{ }^\circ\text{C}$ | | | ± 500 | nA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$ | | | ± 100 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}$ | | | - 25 | |
| | | $V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$ | | | - 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}$ | - 50 | | | mA |
| | | $V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}$ | - 600 | | | |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}, I_D = -25\text{ mA}$ | | | 8 | Ω |
| | | $V_{GS} = -10\text{ V}, I_D = -500\text{ mA}$ | | | 4 | |
| | | $V_{GS} = -10\text{ V}, I_D = -500\text{ mA}, T_J = 125\text{ }^\circ\text{C}$ | | | 6 | |
| Forward Transconductance | g_{fs} | $V_{DS} = -10\text{ V}, I_D = -100\text{ mA}$ | 80 | | | mS |
| Diode Forward Voltage ^a | V_{SD} | $V_{DS} = -200\text{ mA}, V_{GS} = 0\text{ V}$ | 80 | | | V |
| Dynamic | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -30\text{ V}, V_{GS} = -15\text{ V}, I_D \cong -500\text{ mA}$ | | 1.7 | | nC |
| Gate-Source Charge | Q_{gs} | | | 0.26 | | |
| Gate-Drain Charge | Q_{gd} | | | 0.46 | | |
| Input Capacitance | C_{iss} | $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 23 | | pF |
| Output Capacitance | C_{oss} | | | 10 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 5 | | |
| Switching^b | | | | | | |
| Turn-On Time | t_{ON} | $V_{DD} = -25\text{ V}, R_L = 150\text{ }\Omega,$ $I_D \cong -200\text{ mA}, V_{GEN} = -10\text{ V}, R_g = 10\text{ }\Omega$ | | 20 | | ns |
| Turn-Off Time | t_{OFF} | | | 35 | | |

Notes:

 a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

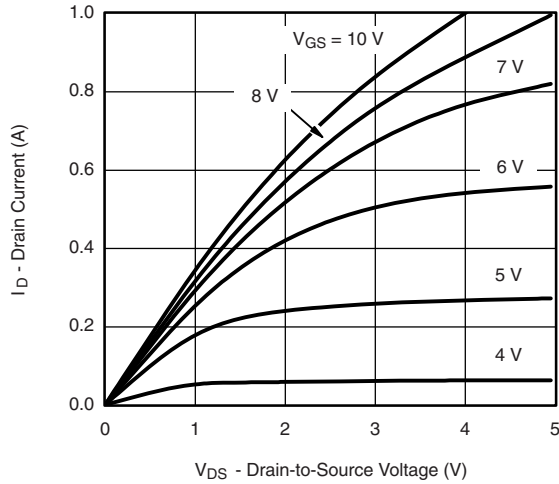
b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

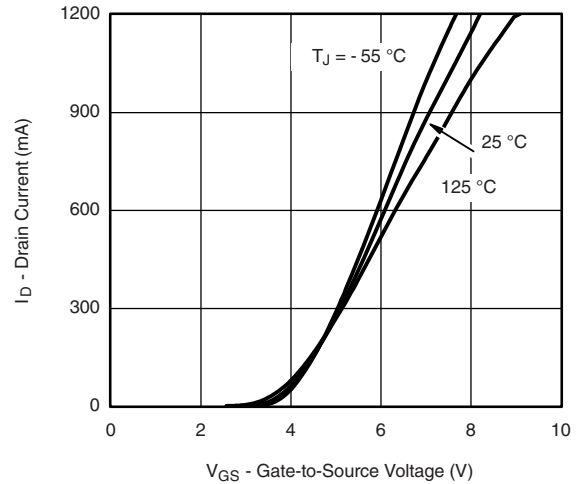


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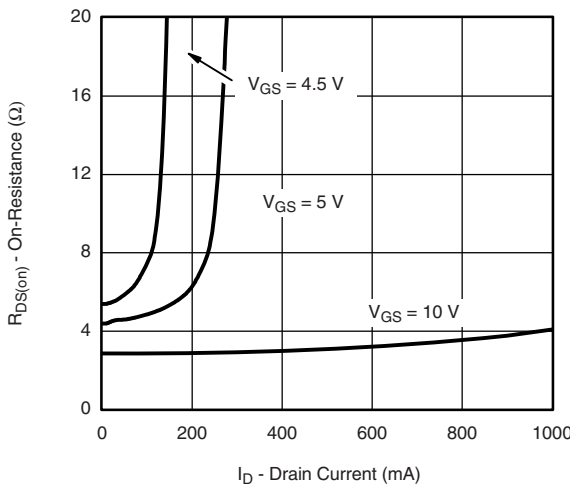
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



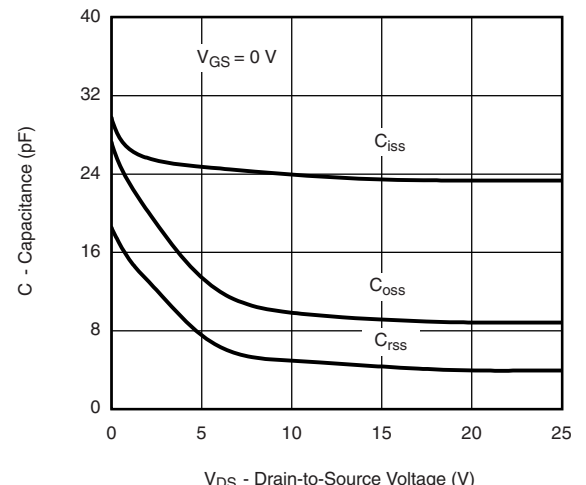
Output Characteristics



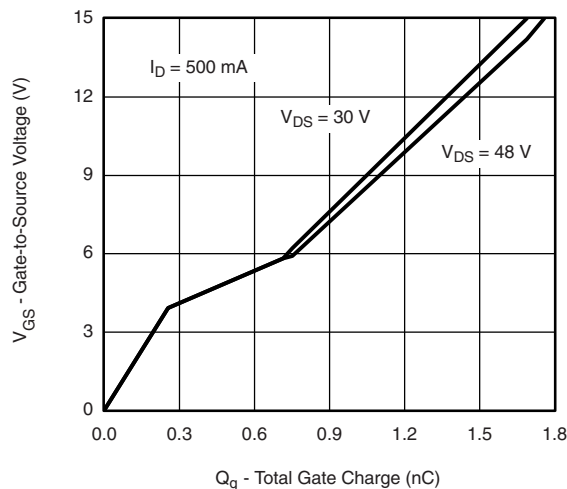
Transfer Characteristics



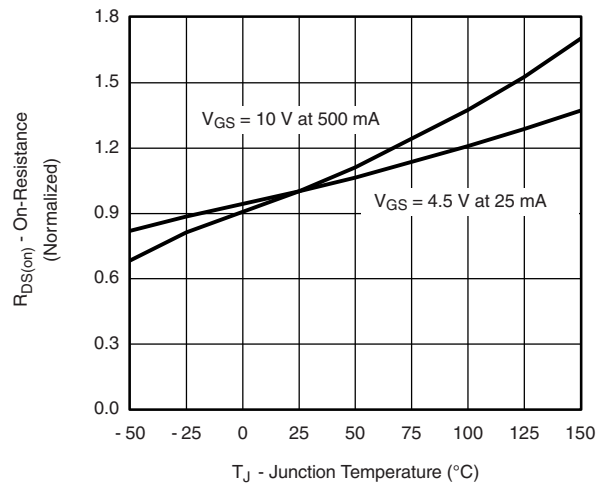
On-Resistance vs. Drain Current



Capacitance



Gate Charge



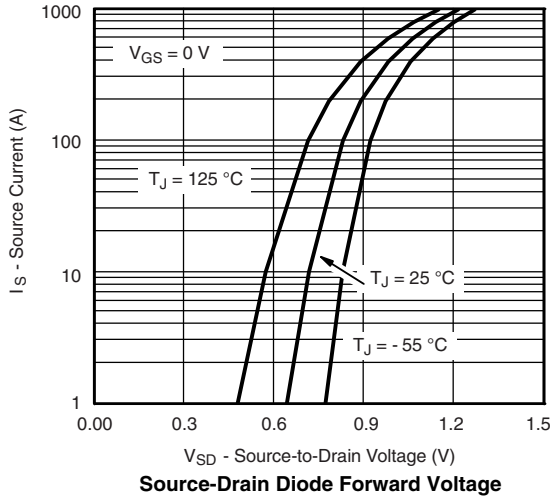
On-Resistance vs. Junction Temperature

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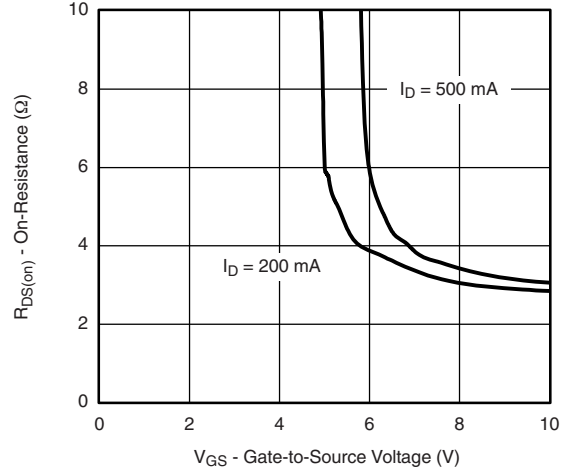
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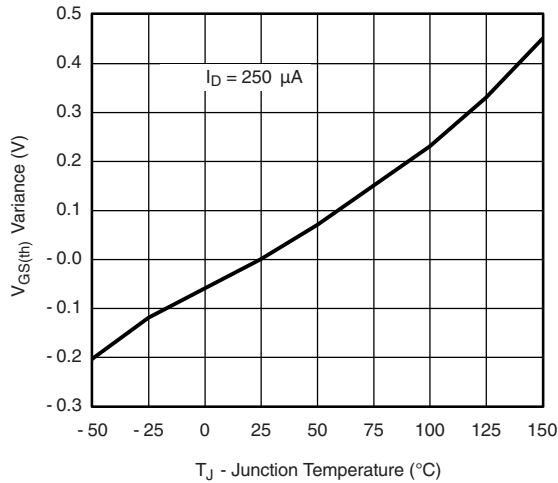
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



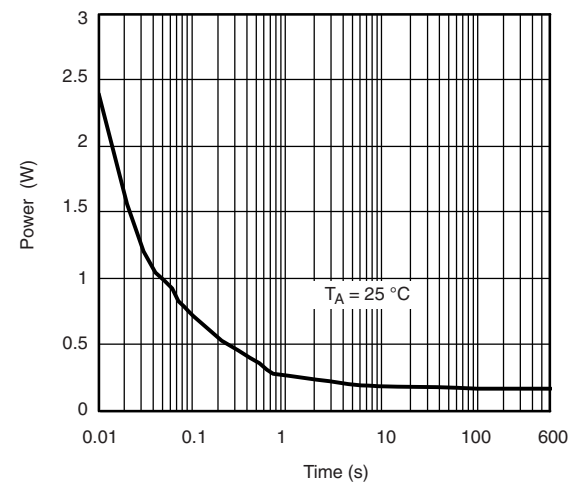
Source-Drain Diode Forward Voltage



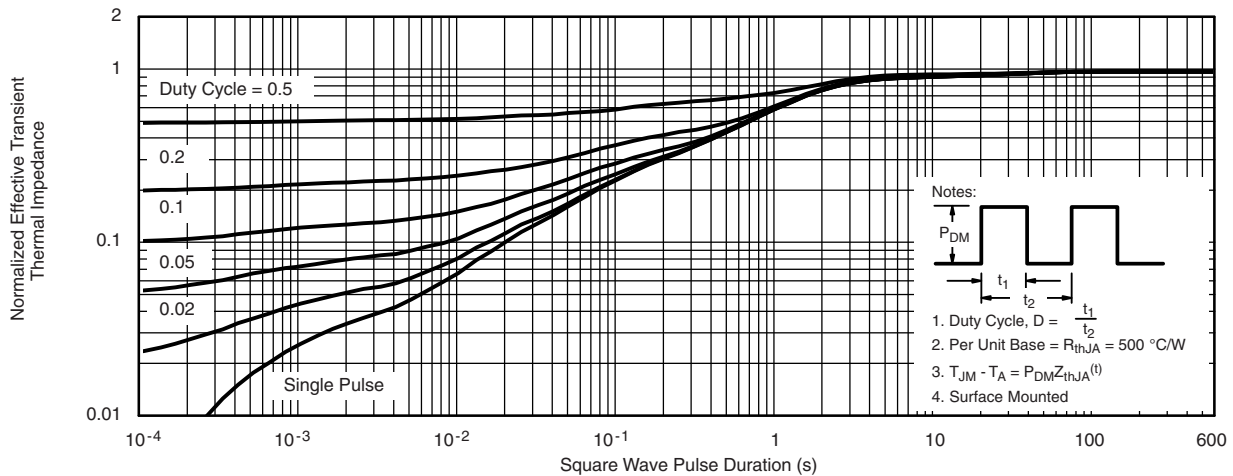
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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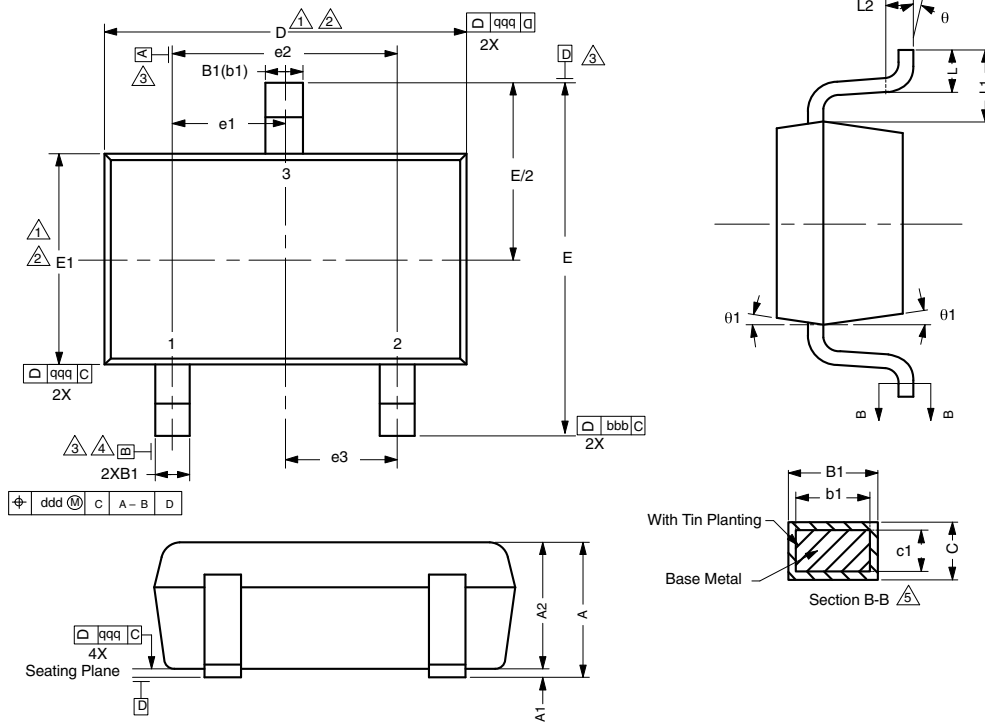


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Package Information

Vishay Siliconix

SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

- 1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- 2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- 3. Datums A, B and D to be determined 0.10 mm from the lead tip.
- 4. Terminal positions are shown for reference only.
- 5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

| DIMENSIONS | TOLERANCES |
|------------|------------|
| aaa | 0.10 |
| bbb | 0.10 |
| ccc | 0.10 |
| ddd | 0.10 |

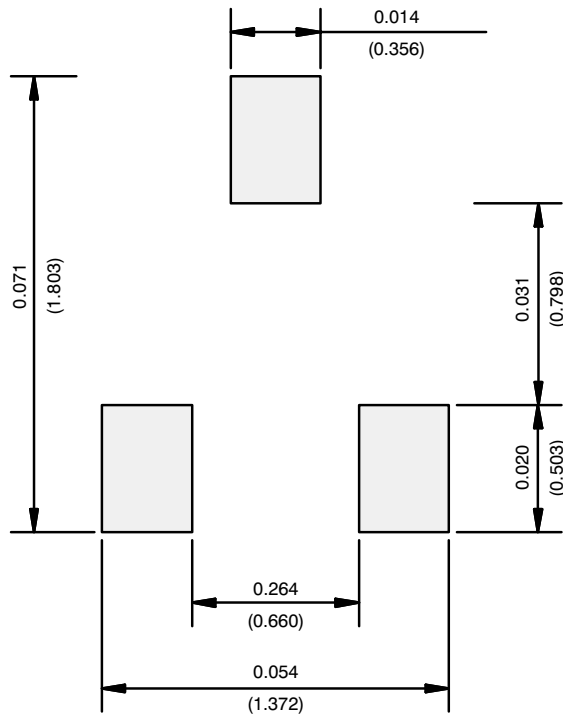
| DIM. | MILLIMETERS | | | NOTE |
|------|-------------|-------|------|------|
| | MIN. | NOM. | MAX. | |
| A | - | - | 0.80 | |
| A1 | 0.00 | - | 0.10 | |
| A2 | 0.65 | 0.70 | 0.80 | |
| B1 | 0.19 | - | 0.24 | 5 |
| b1 | 0.17 | - | 0.21 | |
| c | 0.13 | - | 0.15 | 5 |
| c1 | 0.10 | - | 0.12 | 5 |
| D | 1.48 | 1.575 | 1.68 | 1, 2 |
| E | 1.50 | 1.60 | 1.70 | |
| E1 | 0.66 | 0.76 | 0.86 | 1, 2 |
| e1 | 0.50 BSC | | | |
| e2 | 1.00 BSC | | | |
| e3 | 0.50 BSC | | | |
| L | 0.15 | 0.205 | 0.30 | |
| L1 | 0.40 ref. | | | |
| L2 | 0.15 BSC | | | |
| q | 0° | - | 8° | |
| q1 | 4° | - | 10° | |



Application Note 826

Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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